



ULTRA HIGH DYNAMIC RANGE

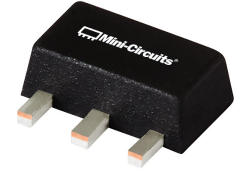
Monolithic Amplifier

PHA-13LN+

50Ω 1MHz to 1GHz

THE BIG DEAL

- Ultra-High IP3, +39 dBm typ.
- Low supply voltage, 3 to 5V
- Excellent Noise Figure, 0.9 dB typ.



Generic photo used for illustration purposes only

CASE STYLE: DF782

APPLICATIONS

- Base station infrastructure
- CATV
- Cellular
- VHF/UHF

+RoHS Compliant

The +Suffix identifies RoHS Compliance. See our website for methodologies and qualifications

PRODUCT OVERVIEW

PHA-13LN+ (RoHS compliant) is an advanced wideband amplifier fabricated using E-PHEMT* technology and offers extremely high dynamic range over a broad frequency range and with low noise figure. In addition, the PHA-13LN+ has good input and output return loss over a broad frequency range. Relatively low supply voltage gives the model advantage in low power consumption. PHA-13LN+ is enclosed in a SOT-89 package and has very good thermal performance.

KEY FEATURES

Feature	Advantages
Broad Band: 1MHz to 1GHz	Broadband covering primary wireless communications bands: VHF, UHF, Cellular
Extremely High IP3 40 dBm typical at 20 MHz 39 dBm typical at 0.5GHz	The PHA-13LN+ matches industry leading IP3 performance relative to device size and power consumption. The combination of the design and E-PHEMT Structure provides enhanced linearity over a broad frequency range as evidence in the IP3 being approximately 15 dB above the P1dB point. This feature makes this amplifier ideal for use in: <ul style="list-style-type: none"> • Driver amplifiers for complex waveform up converter paths • Drivers in linearized transmit systems • Secondary amplifiers in ultra-High Dynamic range receivers
Low Noise Figure 0.9 dB at 0.5 GHz	Enables lower system noise figure performance and along with High OIP3 provides high dynamic range.
Low Supply Voltage, 3 to 5V	PHA-13LN+ supports low supply voltage operation which indicate low power consumption, 3V operation is ideal for battery operated system.

* Enhancement mode pseudomorphic High Electron Mobility Transistor.

REV. A
ECO-010399
PHA-13LN+
MCL NY
221221





ULTRA HIGH DYNAMIC RANGE

Monolithic Amplifier

PHA-13LN+

Mini-Circuits

ELECTRICAL SPECIFICATIONS¹ AT 25°C, 50Ω, UNLESS NOTED OTHERWISE.

Parameter	Condition (MHz)	Vd=5V ¹			Vd=3V ¹	Units
		Min.	Typ.	Max.	Typ.	
Frequency Range		1		1000	1-1000	MHz
Gain	1	22.1	24.6	27.1	23.7	dB
	20	—	24.0	—	23.3	
	250	—	22.8	—	22.1	
	500	20.2	22.4	24.6	21.5	
	1000	—	20.1	—	18.7	
Input Return Loss	1		10.3		9.4	dB
	20		15.4		14.6	
	250		17.5		17.9	
	500		17.4		14.7	
	1000		10.2		7.9	
Output Return Loss	1		11.3		11.0	dB
	20		19.1		21.5	
	250		17.7		20.2	
	500		23.9		20.0	
	1000		8.9		7.8	
Reverse isolation	500		26.1		25.7	dB
Output Power @1 dB compression	1		21.3		15.1	dBm
	20		23.0		16.9	
	250		24.4		19.5	
	500		24.5		19.5	
	1000		24.2		18.7	
Output IP3 ²	1	—	37.0	—	30.6	dBm
	20	—	40.2	—	33.3	
	250	—	40.2	—	33.4	
	500	36	39.0	—	32.3	
	1000	—	36.4	—	28.6	
Noise Figure	1		3.1		3.0	dB
	20		1.2		1.1	
	250		0.9		0.9	
	500		1.0		1.0	
	1000		1.2		1.3	
Device Operating Voltage			5.0		3.0	V
Device Operating Current		—	138.9	162	71.2	mA
Device Current Variation vs. Temperature ³			21.7		30.3	μA/°C
Device Current Variation vs Voltage			0.0338		0.0338	mA/mV
Thermal Resistance, junction-to-ground lead Junction-to-ground lead at 85°C stage temperature			23.3		23.3	°C/W





MAXIMUM RATINGS⁴

Parameter	Ratings
Operating Temperature (ground lead)	-40°C to 105°C
Storage Temperature	-65°C to 150°C
Power Dissipation	3.3 W ⁵
Input Power (CW)	+21 dBm (5 minutes max) ⁶ +6 dBm (continuous) for 1-10 MHz +8 dBm (continuous) for 10-1000 MHz
DC Voltage on Pin 3	10V

4. Permanent damage may occur if any of these limits are exceeded. Electrical maximum ratings are not intended for continuous normal operation.

5. up to 85°C, derate linearly to 2.5 W at 95°C.

6. up to 85°C, derate linearly to 18 dBm at 95°C.

SIMPLIFIED SCHEMATIC AND PIN DESCRIPTION



Function	Pin Number	Description
RF IN	1	RF Input
RF-OUT and DC-IN	3	RF Output and DC Bias
GND	2,4	Connections to ground.

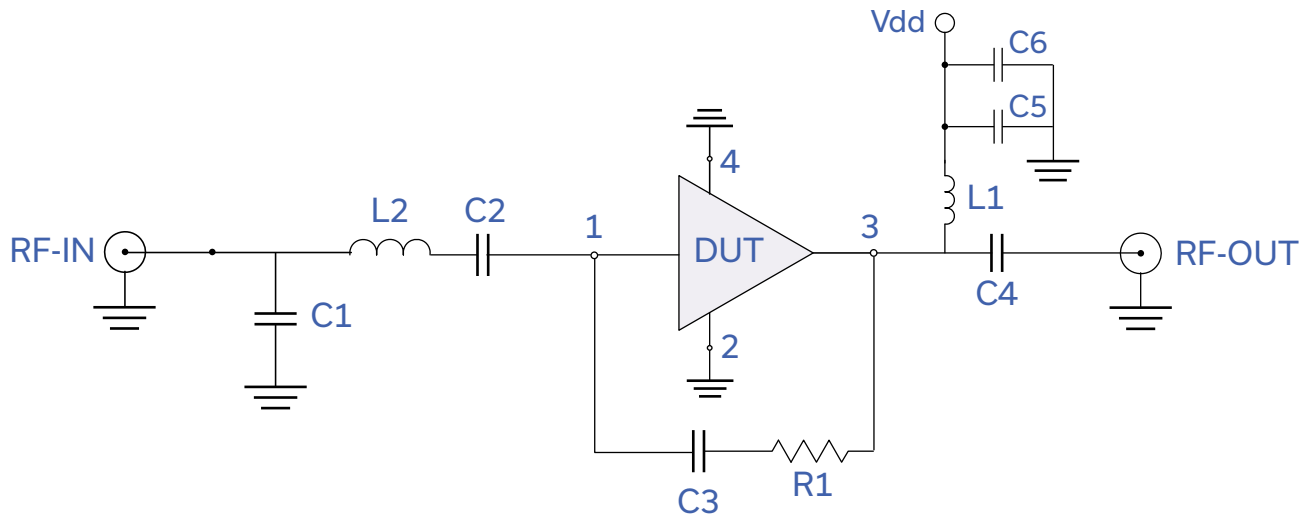
1. Measured on Mini-Circuits Characterization test board TB-969-13LN+. See Characterization Test Circuit (Fig. 1)

2. Tested at Pout= 0 dBm / tone.

3. (Current at 85°C – Current at -45°C)/130



CHARACTERIZATION TEST / RECOMMENDED APPLICATION CIRCUIT



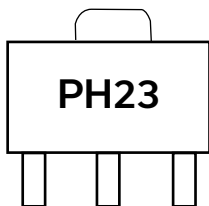
Components	Size	Value	Manufacturer	P/N
C1	0402	1.5 pF	Murata	GRM1555C1H1R5CZ01
C2	0603	2.2 uF		GRM188R61C225KE15
C3	0402	0.1 uF		GRM155R71C104KA88
C4	0603	2.2 uF		GRM188R61C225KE15
C5	0402	1000 pF		GRM1555C1H102JA01
C6	0805	10 uF		GRM21BR61C106KE15
L1	1210	15 uH	Coilcraft	LQH32DN150K53L
L2	0603	5.1 nH	Coilcraft	0603CS-5N1XJL
R1	0402	1500 Ω	Koa	RK73H1ET1501F

Fig 1. Block Diagram of Test Circuit used for characterization. (DUT soldered on Mini-Circuits Characterization test board TB-969-13LN+) Gain, Return loss, Output power at 1dB compression (P1dB), output IP3 (OIP3) and noise figure measured using Agilent's N5242A PNA-X microwave network analyzer.

Conditions:

1. Gain and Return loss: Pin= -25dBm
2. Output IP3 (OIP3): Two tones, spaced 0.5 MHz apart, 0 dBm/ tone at output.

PRODUCT MARKING



Marking may contain other features or characters for internal lot control